

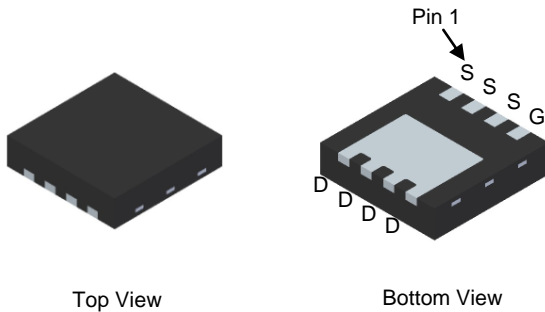
Product Summary

| BV_{DSS} | $R_{DS(ON)}$ Max | I_D $T_C = +25^\circ C$ |
|------------|----------------------------------|------------------------------|
| 100V | 8.8m Ω @ $V_{GS} = 10V$ | 47A |
| | 12.9m Ω @ $V_{GS} = 4.5V$ | 39A |

Description and Applications

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize $R_{DS(ON)}$ and yet maintain superior switching performance. This device is ideal for use in notebook battery power management and loadswitch.

- Backlighting
- Power Management Functions
- DC-DC Converters



Top View

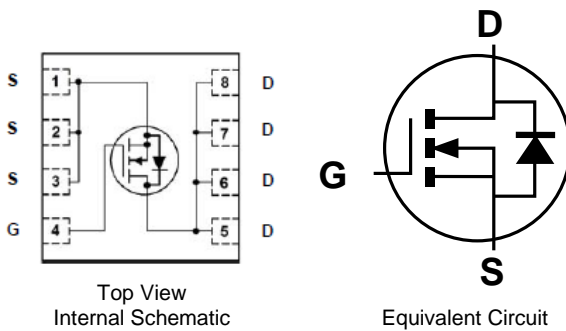
Bottom View

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- High Conversion Efficiency
- Low $R_{DS(ON)}$ – Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

- Case: V-DFN3333-8 (Type B)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Below Diagram
- Terminals: Finish –NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.03 grams (Approximate)



Top View
Internal Schematic

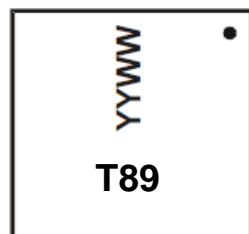
Equivalent Circuit

Ordering Information (Note 4)

| Part Number | Case | Packaging |
|-----------------|----------------------|-------------------|
| DMT10H009LCG-7 | V-DFN3333-8 (Type B) | 2,000/Tape & Reel |
| DMT10H009LCG-13 | V-DFN3333-8 (Type B) | 3,000/Tape & Reel |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



T89 = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 18 = 2018)
 WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Unit |
|--|--------------|------------------------|------------------|-------|------|
| Drain-Source Voltage | | | V _{DSS} | 100 | V |
| Gate-Source Voltage | | | V _{GSS} | ±20 | V |
| Continuous Drain Current, V _{GS} = 10V (Note 6) | Steady State | T _A = +25°C | I _D | 12.4 | A |
| | | T _A = +70°C | | 9.9 | |
| Continuous Drain Current, V _{GS} = 10V | Steady State | T _C = +25°C | I _D | 47 | A |
| | | T _C = +70°C | | 37 | |
| Maximum Continuous Body Diode Forward Current (Note 6) | | | I _S | 22 | A |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) | | | I _{DM} | 160 | A |
| Pulsed Body Diode Continuous Current (10µs Pulse, Duty Cycle = 1%) | | | I _{SM} | 160 | A |
| Avalanche Current, L = 0.3mH (Note 8) | | | I _{AS} | 21 | A |
| Avalanche Energy, L = 0.3mH (Note 8) | | | E _{AS} | 66 | mJ |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|--|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 5) | P _D | 1 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | R _{θJA} | 129 | °C/W |
| Total Power Dissipation (Note 6) | P _D | 2.1 | W |
| Thermal Resistance, Junction to Ambient (Note 6) | R _{θJA} | 59 | °C/W |
| Thermal Resistance, Junction to Case | R _{θJC} | 4.2 | °C/W |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C |

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|---|---------------------|-----|------|------|------|--|
| OFF CHARACTERISTICS (Note 7) | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 100 | — | — | V | V _{GS} = 0V, I _D = 1mA |
| Zero Gate Voltage Drain Current | I _{DSS} | — | — | 1 | µA | V _{DS} = 80V, V _{GS} = 0V |
| Gate-Source Leakage | I _{GSS} | — | — | ±100 | nA | V _{GS} = ±20V, V _{DS} = 0V |
| ON CHARACTERISTICS (Note 7) | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | 1.1 | — | 2.5 | V | V _{DS} = V _{GS} , I _D = 250µA |
| Static Drain-Source On-Resistance | R _{DS(ON)} | — | 7.2 | 8.8 | mΩ | V _{GS} = 10V, I _D = 20A |
| | | — | 9.8 | 12.9 | mΩ | V _{GS} = 4.5V, I _D = 5A |
| Diode Forward Voltage | V _{SD} | — | 0.8 | 1.2 | V | V _{GS} = 0V, I _S = 20A |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | | |
| Input Capacitance | C _{ISS} | — | 2309 | — | pF | V _{DS} = 50V, V _{GS} = 0V f = 1MHz |
| Output Capacitance | C _{OSS} | — | 536 | — | | |
| Reverse Transfer Capacitance | C _{ISS} | — | 13.7 | — | | |
| Gate Resistance | R _G | — | 1.9 | — | Ω | V _{DS} = 0V, V _{GS} = 0V, f = 1MHz |
| Total Gate Charge | Q _g | — | 20.2 | — | nC | V _{DD} = 50V, I _D = 20A, V _{GS} = 4.5V |
| Gate-Source Charge | Q _{gs} | — | 7.0 | — | | |
| Gate-Drain Charge | Q _{gd} | — | 8.5 | — | | |
| Turn-On Delay Time | t _{D(ON)} | — | 5.4 | — | ns | V _{DD} = 50V, V _{GS} = 10V, I _D = 20A, R _G = 3Ω |
| Turn-On Rise Time | t _R | — | 10.6 | — | | |
| Turn-Off Delay Time | t _{D(OFF)} | — | 28.3 | — | | |
| Turn-Off Fall Time | t _F | — | 14.9 | — | | |
| Reverse Recovery Time | t _{RR} | — | 44.3 | — | ns | I _F = 20A, di/dt = 100A/µs |
| Reverse Recovery Charge | Q _{RR} | — | 65.5 | — | nC | |

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

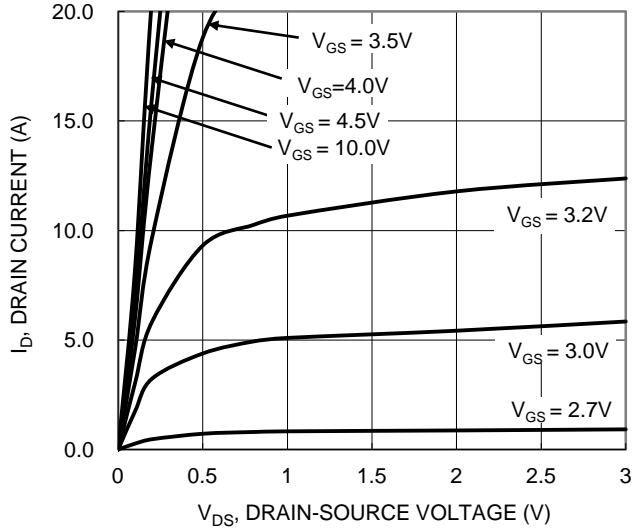


Figure 1. Typical Output Characteristic

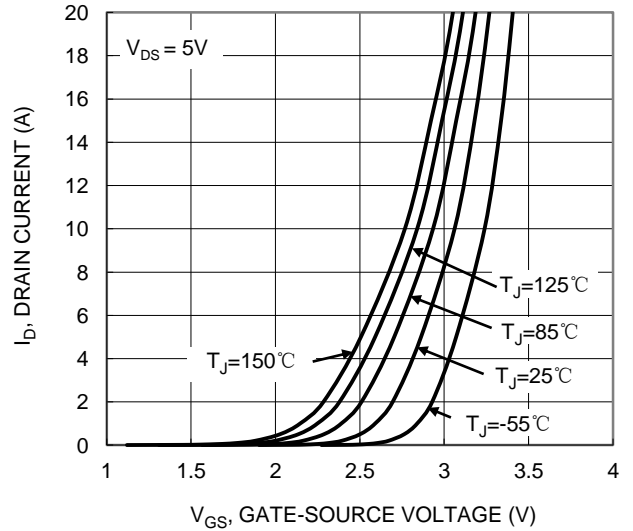


Figure 2. Typical Transfer Characteristic

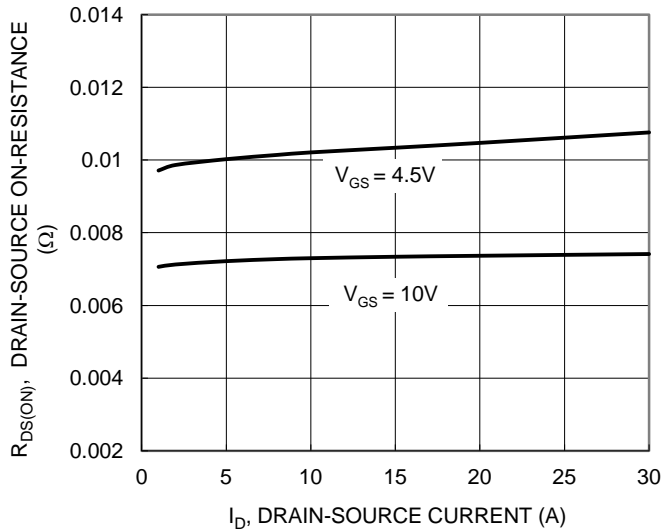


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

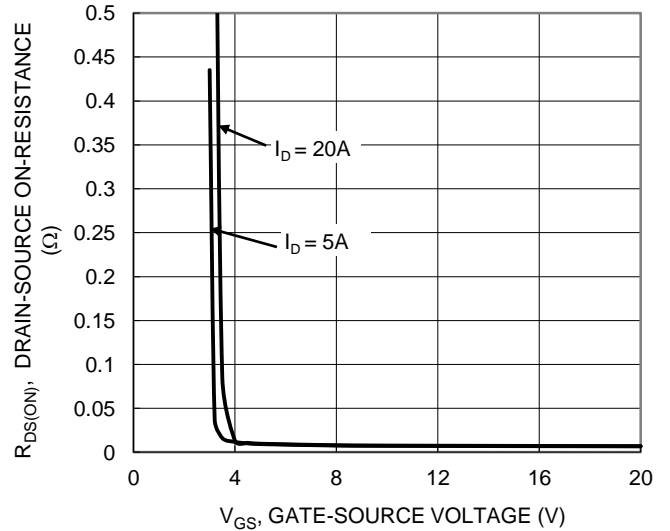


Figure 4. Typical Transfer Characteristic

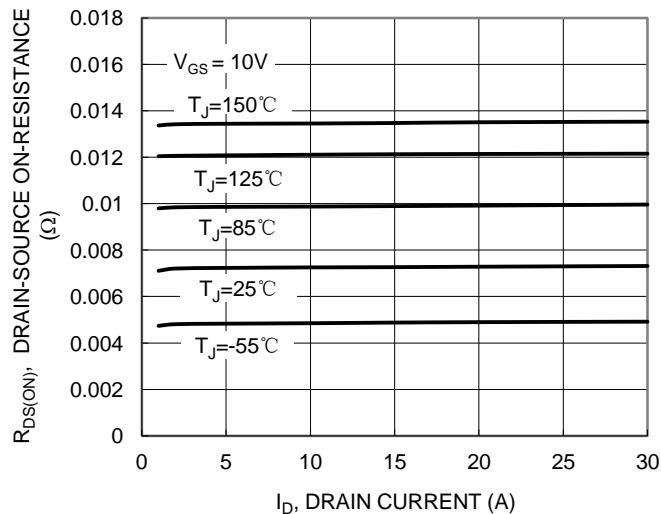


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

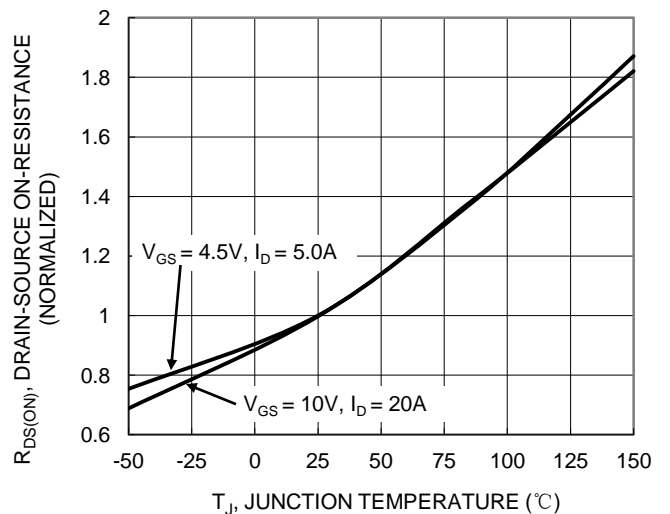


Figure 6. On-Resistance Variation with Junction Temperature

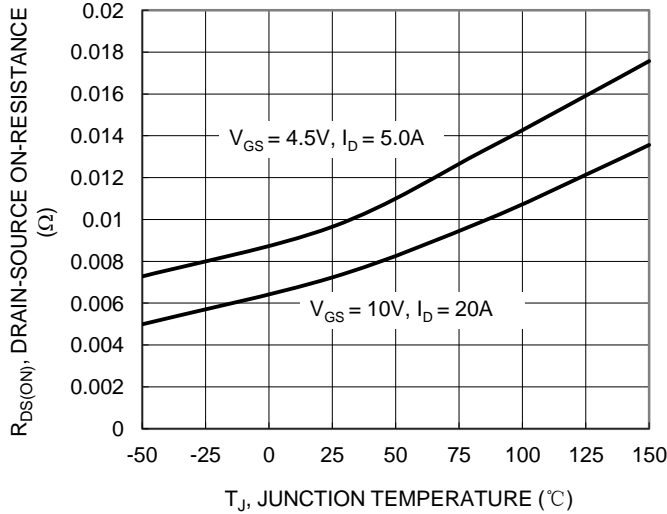


Figure 7. On-Resistance Variation with Junction Temperature

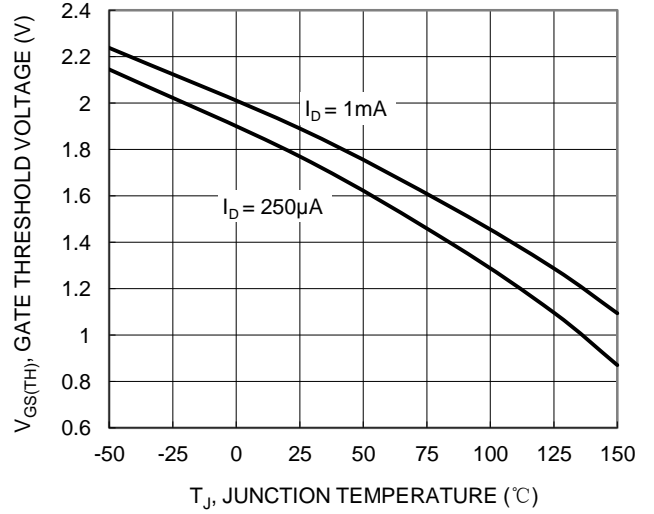


Figure 8. Gate Threshold Variation vs. Junction Temperature

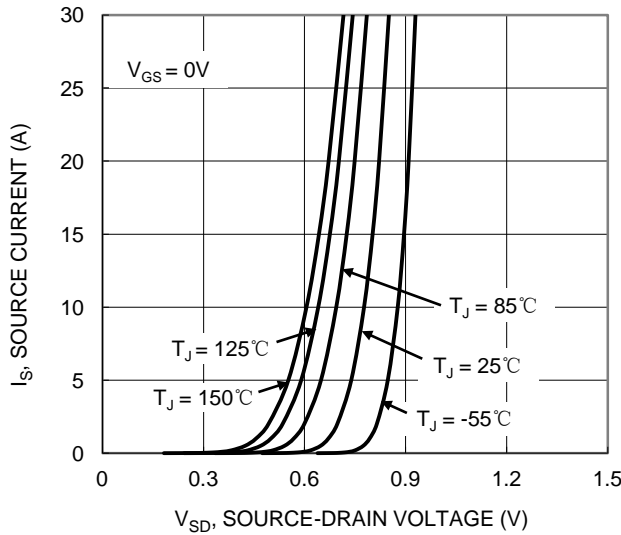


Figure 9. Diode Forward Voltage vs. Current

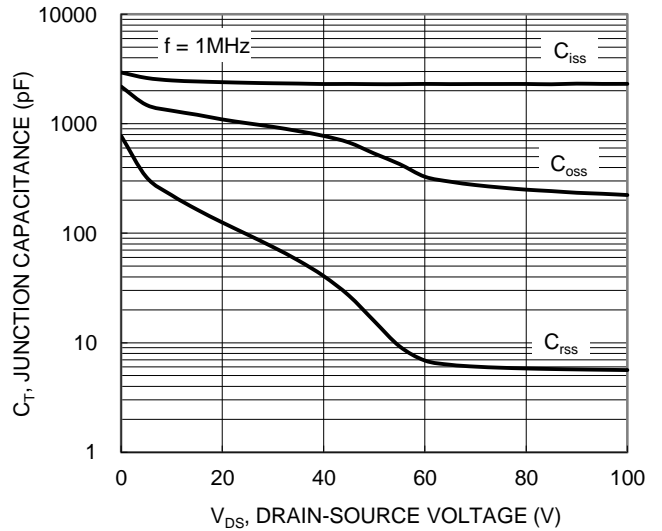


Figure 10. Typical Junction Capacitance

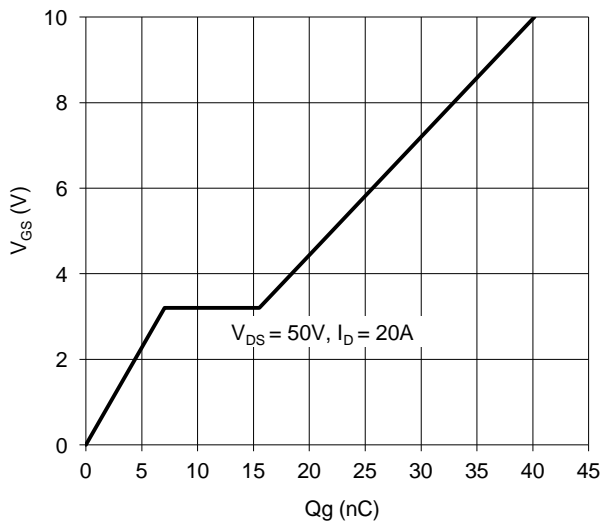


Figure 11. Gate Charge

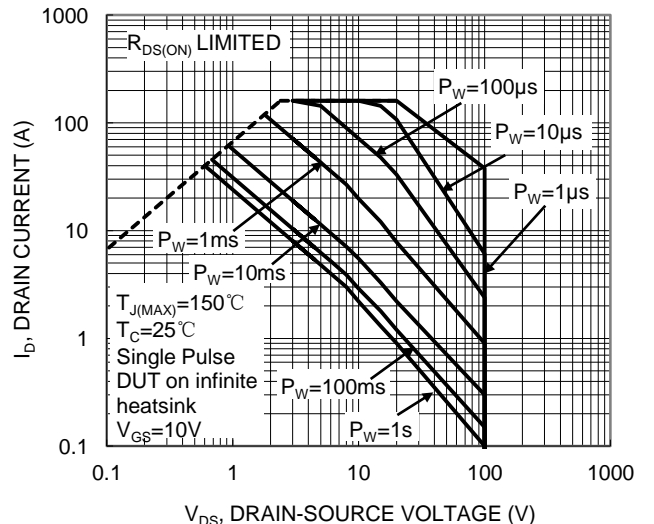


Figure 12. SOA, Safe Operation Area

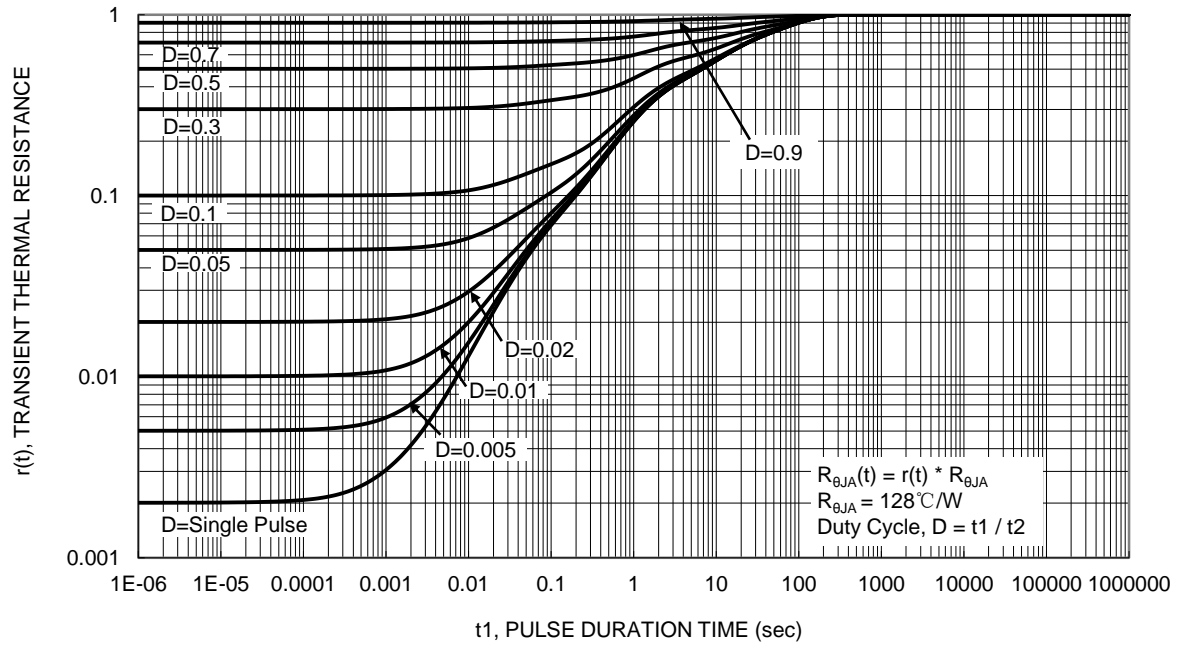
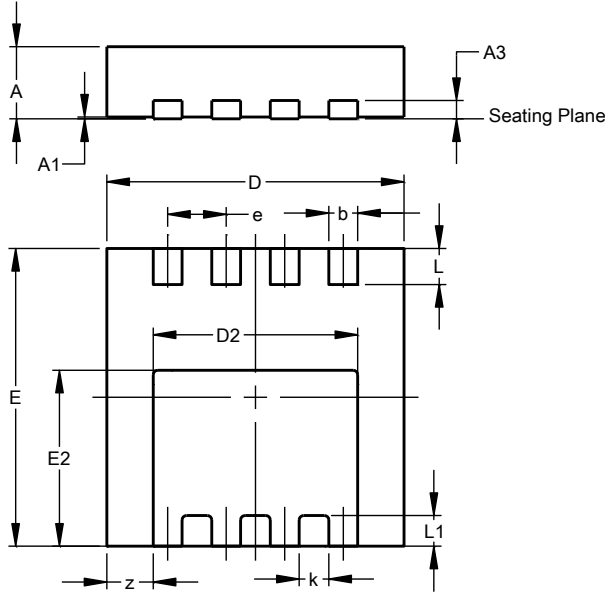


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

V-DFN3333-8 (Type B)

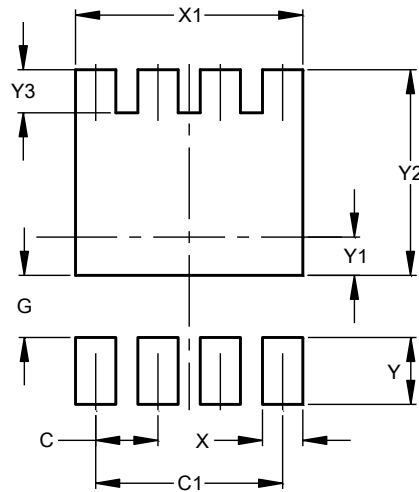


| V-DFN3333-8 (Type B) | | | |
|-------------------------|------|------|-------|
| Dim | Min | Max | Typ |
| A | 0.75 | 0.85 | 0.80 |
| A1 | 0.00 | 0.05 | 0.02 |
| A3 | -- | -- | 0.203 |
| b | 0.27 | 0.37 | 0.32 |
| D | 3.25 | 3.35 | 3.30 |
| D2 | 2.17 | 2.37 | 2.27 |
| E | 3.25 | 3.35 | 3.30 |
| E2 | 1.85 | 2.05 | 1.95 |
| e | -- | -- | 0.65 |
| k | -- | -- | 0.33 |
| L | 0.35 | 0.45 | 0.40 |
| L1 | -- | -- | 0.34 |
| z | -- | -- | 0.515 |
| All Dimensions in mm | | | |

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

V-DFN3333-8 (Type B)



| Dimensions | Value (in mm) |
|------------|---------------|
| C | 0.650 |
| C1 | 1.950 |
| G | 0.650 |
| X | 0.420 |
| X1 | 2.370 |
| Y | 0.700 |
| Y1 | 0.400 |
| Y2 | 2.150 |
| Y3 | 0.450 |

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